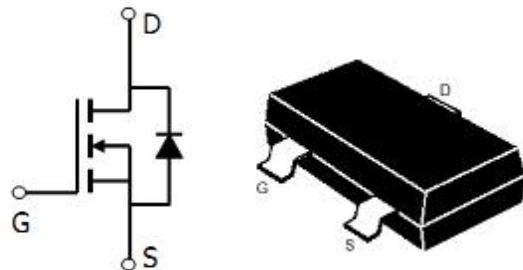


GM3100

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



### N-Channel Enhancement-Mode MOS FETs

N 溝道增強型 MOS 場效應管

#### ■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	30	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 20$	V
Drain Current (continuous) 漏極電流-連續	$I_D$	8	A
Drain Current (pulsed) 漏極電流-脉沖	$I_{DM}$	20	A
Total Device Dissipation 總耗散功率 $TA=25^{\circ}\text{C}$ 環境溫度為 $25^{\circ}\text{C}$	$P_D$	1400	mW
Junction 結溫	$T_J$	150	$^{\circ}\text{C}$
Solder Temperature/Solder Time 焊接溫度/焊接時間	$T/t$	260/10	$^{\circ}\text{C}/\text{S}$
Storage Temperature 儲存溫度	$T_{stg}$	-55 to +150	$^{\circ}\text{C}$

#### ■DEVICE MARKING 打標

GM3100=3100
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GM3100

### ■ELECTRICAL CHARACTERISTICS 電特性

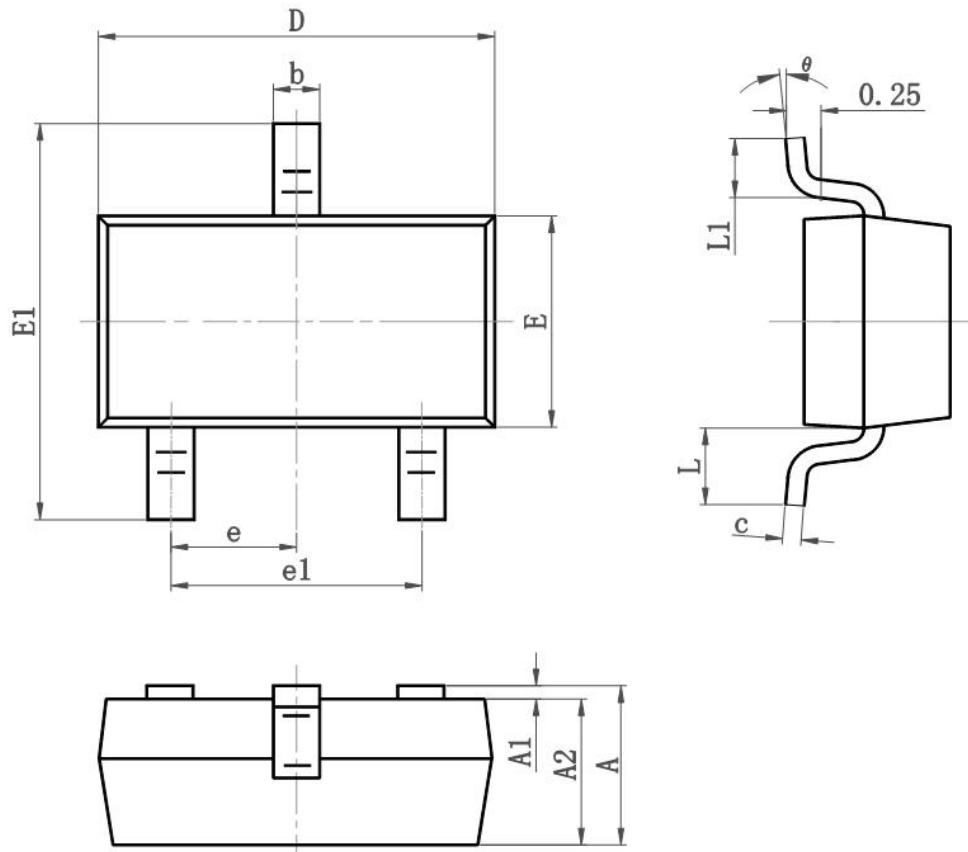
( $T_A=25^\circ\text{C}$  unless otherwise noted 如無特殊說明，溫度為  $25^\circ\text{C}$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極 - 源極擊穿電壓( $I_D = 250\mu\text{A}, V_{GS}=0\text{V}$ )	$\text{BV}_{DSS}$	30	—	—	V
Gate Threshold Voltage 柵極開啓電壓( $I_D = 250\mu\text{A}, V_{GS} = V_{DS}$ )	$V_{GS(\text{th})}$	1	—	2	V
Diode Forward Voltage Drop 內附二極管正向壓降( $I_S=1\text{A}, V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	1.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流( $V_{GS}=0\text{V}, V_{DS}= 24\text{V}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate Body Leakage 柵極漏電流( $V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻( $I_D= 5\text{A}, V_{GS}= 10\text{V}$ )	$R_{DS(\text{ON})}$	—	12	14	$\text{m}\Omega$
Static Drain-Source On-State Resistance 静态漏源導通電阻( $I_D= 3.5\text{A}, V_{GS}= 4.5\text{V}$ )	$R_{DS(\text{ON})}$	—	14	16	$\text{m}\Omega$
Input Capacitance 輸入電容 ( $V_{GS}=0\text{V}, V_{DS}= 10\text{V}, f=1\text{MHz}$ )	$C_{ISS}$	—	600	—	pF
Output Capacitance 輸出電容 ( $V_{GS}=0\text{V}, V_{DS}= 10\text{V}, f=1\text{MHz}$ )	$C_{OSS}$	—	120	—	pF
Turn-ON Time 开啓時間 ( $V_{DS}= 10\text{V}, I_D= 3\text{A}, R_{GEN}=6\Omega$ )	$t_{(\text{on})}$	—	8	—	ns
Turn-OFF Time 矩斷時間 ( $V_{DS}= 10\text{V}, I_D= 3\text{A}, R_{GEN}=6\Omega$ )	$t_{(\text{off})}$	—	60	—	ns

Pulse Width  $\leq 300 \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$

GM3100

■DIMENSION 外形封裝尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.500	1.700	0.059	0.067
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°